



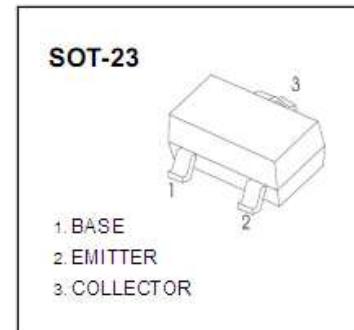
印章/Marking: M6

特点/Features:

- 1、 h_{FE} 大, $h_{FE}=200 \sim 1000$;
- 2、 h_{FE} 线性特性好,

用途/Applications:

用于低电平、低噪声的前置放大器, 与 S9014 互补。



极限参数/Absolute maximum ratings (Ta=25°C)

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
集电极-基极电压/Collector-Base Voltage	V_{CBO}	-50	V
集电极-发射极电压/Collector-Emitter Voltage	V_{CEO}	-45	V
发射极-基极电压/Emitter-Base Voltage	V_{EBO}	-5	V
集电极连续电流/Collector Current Continuous	I_c	-0.1	A
集电极耗散功率/Collector Power Dissipation	P_c	0.2	W
结温/Junction Temperature	T_j	150	°C
储存温度/Storage Temperature	T_{stg}	-55~150	°C

电性能参数/Electrical characteristics (Ta=25°C)

参数	符号	测试条件	最小值	最大值	单位
集电极-基极击穿电压	$V_{BR(CBO)}$	$I_c=-100 \mu A, I_E=0$	-50		V
集电极-发射极击穿电压	$V_{BR(CEO)}$	$I_c=-100 \mu A, I_B=0$	-45		V
发射极-基极击穿电压	$V_{BR(EBO)}$	$I_E=-100 \mu A, I_c=0$	-5		V
集电极截止电流	I_{CBO}	$V_{CB}=-50V, I_E=0$		-0.1	μA
发射极截止电流	I_{EBO}	$V_{EB}=-5V, I_c=0$		-0.1	μA
直流电流增益	h_{FE}	$V_{CE}=-5V, I_c=-1mA$	200	1000	
集电极-发射极饱和压降	$V_{CE(sat)}$	$I_c=-100mA, I_B=-10mA$		-0.3	V
基极-发射极饱和压降	$V_{BE(sat)}$	$I_c=-100mA, I_B=-10mA$		-1	V
特征频率	f_T	$V_{CE}=-5V, I_c=-10mA, f=30MHz$	150		MHz

h_{FE} 分档/Classification of h_{FE}

档位/Rank	L	H
范围/Range	200~450	450~1000

典型特性曲线图/Typical Characteristics

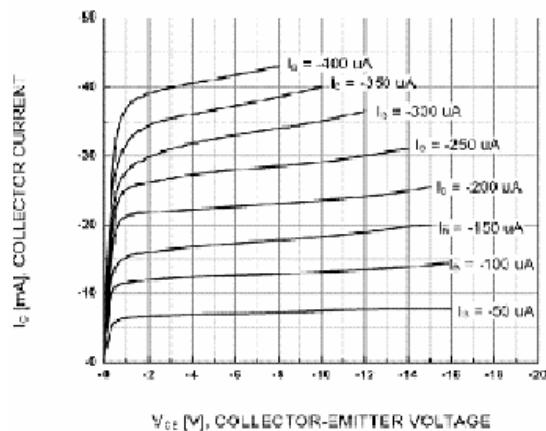


Figure 1. Static Characteristic

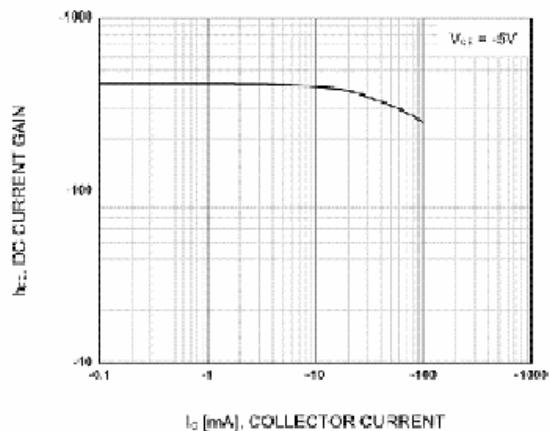


Figure 2. DC current Gain

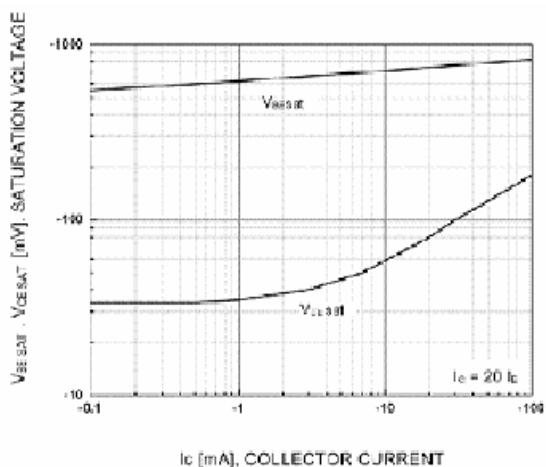


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

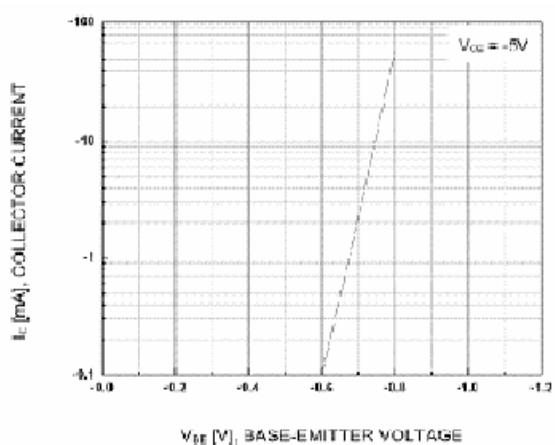


Figure 4. Base-Emitter On Voltage

